



EXHIBIT A: AMENDMENTS TO THE CLAIMS

1. (Amended) A method for making a thin film transistor containing a gate dielectric structure, comprising:

providing a substrate for the gate dielectric structure; and

providing an oxide layer of the gate [oxide] dielectric structure on the substrate by an in-situ steam generation process.

9. (Amended) A method for making a semiconductor device, comprising:

providing a substrate; and

providing a gate dielectric structure by:

providing a first oxide layer on the substrate by an in-situ steam generation process;

providing a nitride layer on the oxide layer; and

providing a second oxide layer on the nitride layer.

24. (Amended) A SONOS semiconductor device made by the method comprising:

providing a substrate; and

providing a gate dielectric structure by:

providing a first oxide layer on the substrate by an in-situ steam generation process;

providing a nitride layer on the oxide layer; and

providing a second oxide layer on the nitride layer.

26. (Amended) An integrated circuit containing a SONOS semiconductor device made by the method comprising:

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providing a substrate; and

providing a gate dielectric structure by:

providing a first oxide layer on the substrate by an in-situ steam generation process;

providing a nitride layer on the oxide layer; and

providing a second oxide layer on the nitride layer.